

## Guidelines for Abstract Preparation of EDISON 22 (Bold, 12 point, Times or Times New Roman)

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A **one-page abstract** should be prepared on an A4-size paper with 2 cm margins all around and **uploaded in the pdf format**. Templates are provided in LaTeX, Word and Open Document format. Authors who prefer a different typesetting system, please adhere to the following guidelines. Please do not change the style of the abstract (font types, sizes, spacings, margins, etc.). The submission deadline is **15 March 2023**.

The abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address of the corresponding author. In the title capital letters should be used for the initial letter of each word except articles, prepositions and conjunctions. The main text should be typed single-spaced and at 11 point. The numbered list of all references should appear at the end of the abstract. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. Figures can be included; they should be numbered consecutively and accompanied by a figure caption in 10 point below the figure. Please do not generate page numbers.

When uploading your abstract you may indicate your preference for an oral or a poster presentation. Furthermore, please specify the tentative speaker/presenter and the category which is most appropriate for your contribution:

1. Nonequilibrium electrical and thermal transport in bulk, nanostructures and devices
2. Terahertz phenomena in semiconductor materials and devices
3. Mesoscopic phenomena in nanostructures
4. Electrical and optical properties of 2D materials and their heterostructures
5. Carrier dynamics and ultra-fast optical phenomena
6. Coherent carrier dynamics for quantum technologies
7. Semiconductor-based spintronics
8. Electronic properties of topological materials
9. Carrier dynamics in organic materials
10. Charge dynamics in energy conversion and energy harvesting processes
11. Fluctuations and noise in nonequilibrium carrier dynamics
12. Interaction of charges with plasmonic, phononic and mechanical excitations

### References

- [1] J. Bardeen and W. H. Brattain, Phys. Rev. **75**, 1208 (1949).  
[2] A. Einstein, B. Podolsky, and N. Rosen, Phys. Rev. **47**, 777 (1935).



Fig. 1. EDISON 22 logo (caption 10 point, Times or Times New Roman)